

A semiconductor component includes a semiconductor body having a substrate of a first conduction type and a first layer of a second conduction type that is located above the substrate. A channel zone of the first conduction type is formed in the first layer. A first terminal zone of the second conduction type is configured adjacent the channel zone. A second terminal zone of the first conduction type is formed in the first layer. Compensation zones of the first conduction type are formed in the first layer. A second layer of the second conduction type is configured between the substrate and the compensation zones.